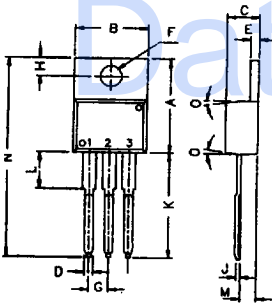
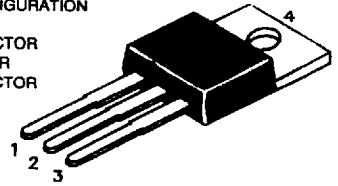


MJE2955T PNP PLASTIC POWER TRANSISTOR
 MJE3055T NPN PLASTIC POWER TRANSISTOR
 General Purpose Amplifier and Switching Applications

- PIN CONFIGURATION
 1. BASE
 2. COLLECTOR
 3. EMITTER
 4. COLLECTOR



ALL DIMENSIONS ARE IN M.M.

DIM	MIN	MAX
A	14,42	16,51
B	9,63	10,67
C	3,56	4,83
D	-	0,90
E	1,15	1,40
F	3,75	3,88
G	2,29	2,79
H	2,54	3,43
J	-	0,56
K	12,70	14,73
L	-	6,35
M	2,03	2,92
N	-	31,24
O	7 DEG	

ABSOLUTE MAXIMUM RATINGS

Collector-base voltage (open emitter)	V_{CBO}	max.	70 V
Collector-emitter voltage (open base)	V_{CEO}	max.	60 V
Collector current	I_C	max.	10 A
Total power dissipation up to $T_C = 25^\circ\text{C}$	P_{tot}	max.	75 W
Junction temperature	T_j	max.	150 °C
Collector-emitter saturation voltage	V_{CEsat}	max.	1.1 V
$I_C = 4 \text{ A}; I_B = 0.4 \text{ A}$			
D.C. current gain	h_{FE}	min	20
$I_C = 4 \text{ A}; V_{CE} = 4 \text{ V}$		max.	100

RATINGS (at $T_A=25^\circ\text{C}$ unless otherwise specified)

Limiting values

Collector-base voltage (open emitter)	V_{CBO}	max.	0 V
Collector-emitter voltage (open base)	V_{CEO}	max.	60 V
Emitter-base voltage (open collector)	V_{EBO}	max.	5.0 V

Collector current	I_C	max.	10 A
Base current	I_B	max.	6 A
Total power dissipation up to $T_C = 25^\circ\text{C}$	P_{tot}	max.	75 W
Derate above 25°C		max.	0.6 W/ $^\circ\text{C}$
Junction temperature	T_j	max.	150 $^\circ\text{C}$
Storage temperature	T_{stg}		-65 to +150 $^\circ\text{C}$

THERMAL RESISTANCE

From junction to case	$R_{th\ j-c}$	=	1.67 $^\circ\text{C}/\text{W}$
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CHARACTERISTICS

$T_{amb} = 25^\circ\text{C}$ unless otherwise specified

Collector cutoff current

$I_E = 0; V_{CB} = 70\text{V}$	I_{CBO}	max.	1.0 mA
$I_E = 0; V_{CB} = 70\text{V}; T_C = 150^\circ\text{C}$	I_{CBO}	max.	10 mA
$V_{EB(off)} = 1.5\text{V}; V_{CE} = 70\text{V}$	I_{CEX}	max.	1.0 mA
$V_{EB(off)} = 1.5\text{V}; V_{CE} = 70\text{V}; T_C = 150^\circ\text{C}$	I_{CEX}	max.	5.0 mA
$I_B = 0; V_{CE} = 30\text{V}$	I_{CEO}	max.	0.7 mA

Emitter cut-off current

$I_C = 0; V_{EB} = 5\text{V}$	I_{EBO}	max.	5 mA
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Breakdown voltages

$I_C = 200\text{ mA}; I_B = 0$	$V_{CEO(sus)}^*$	min.	60 V
$I_C = 1\text{ mA}; I_E = 0$	V_{CBO}	min.	70 V
$I_E = 1\text{ mA}; I_C = 0$	V_{EBO}	min.	5.0 V

Saturation voltages

$I_C = 4\text{ A}; I_B = 0.4\text{ A}$	V_{CEsat}^*	max.	1.1 V
$I_C = 10\text{ A}; I_B = 3.3\text{ A}$	V_{CEsat}^*	max.	8.0 V

Base-emitter on voltage

$I_C = 4\text{ A}; V_{CE} = 4\text{ V}$	$V_{BE(on)}^*$	max.	1.8 V
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D.C. current gain

$I_C = 4\text{ A}; V_{CE} = 4\text{ V}$	h_{FE}^*	min.	20
		max.	100

$I_C = 10\text{ A}; V_{CE} = 4\text{ V}$	h_{FE}^*	min.	5
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Transition frequency

$I_C = 0.5\text{ A}; V_{CE} = 10\text{ V}; f = 500\text{ KHz}$	f_T	min.	2.0 MHz
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* Pulse test: pulse width $\leq 300\ \mu\text{s}$; duty cycle $\leq 2\%$.